IN THE CLAIMS:

Please amend claims 11 and 15 and add new claims 17 and 18 as follows.

1.-10. (Canceled)

11. (Currently Amended) An RF device comprising:

a plurality of semiconductor elements formed on a semiconductor substrate;

and

a plurality of through holes which are provided between two adjacent ones of the plurality of semiconductor elements and pass from a surface through the backside of the semiconductor substrate;

wherein a distance between two adjacent ones of the plurality of through holes is smaller than a thickness of the semiconductor substrate so as to reduce power leaking between two adjacent ones of the plurality of semiconductor elements.

12. (Previously Presented) The device of claim 11, wherein side faces of the plurality of through holes are covered with a conductive material.

13. (Previously Presented) The device of claim 12, wherein the conductive material is electrically connected to a ground wiring layer provided on the surface of the backside of the semiconductor substrate.

14. (Previously Presented) The device of claim 11, wherein the semiconductor substrate is a GaAs substrate.

15. (Currently Amended) An RF device comprising:

a plurality of semiconductor elements formed on a semiconductor substrate;

a first group of through holes which are provided between two adjacent ones of the plurality of semiconductor elements and pass from a surface through the backside of the semiconductor substrate and whose side faces are covered with a conductive material; and

a second group of through holes which are provided in electrodes of the plurality of semiconductor elements, pass from a surface through the backside of the semiconductor substrate, and whose side faces are covered with conductive material,

wherein the conductive material which covers side faces of the first and second groups of through holes is electrically connected to a wiring layer provided on the backside of the semiconductor substrate, and

a distance between two adjacent ones of the first group of through holes is smaller than a thickness of the semiconductor substrate so as to reduce power leaking between two adjacent ones of the plurality of semiconductor elements.

16. (Previously Presented) The device of claim 15, wherein the semiconductor substrate is a GaAs substrate.

17. (New) The RF device of claim 11,

wherein the distance between two adjacent ones of the plurality of through holes is smaller than a thickness of the semiconductor substrate so as to exponentially reduce power leaking between two adjacent ones of the plurality of semiconductor elements with regard to the distance between two adjacent ones of the plurality of through holes.

18. (New) The RF device of claim 15,

wherein the distance between two adjacent ones of the first group of through holes is smaller than a thickness of the semiconductor substrate so as to exponentially reduce power leaking between two adjacent ones of the plurality of semiconductor elements with regard to the distance between two adjacent ones of the first group of through holes.